Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A photoelectric transducer comprising a first pin junction part including:

a first p-layer;

a first n-layer disposed so as to oppose the first p-layer; and

a first i-layer, disposed between the first p-layer and first n-layer, containing an iron atom, a silicon atom bonded to the iron atom, and a hydrogen atom.

2. (Original) A photoelectric transducer according to claim 1, wherein the first i-layer is formed by at least partly bonding the hydrogen atom to the silicon atom or iron atom.

3. (Currently Amended) A photoelectric transducer according to claim 1~~ or 2~~, wherein the first i-layer is mainly amorphous.

4. (Currently Amended) A photoelectric transducer according to ~~one of claims 1 to 3~~claim 1, wherein the first i-layer has a hydrogen atom content of 1 to 25 atom %.

5. (Currently Amended) A photoelectric transducer according to ~~one of claims 1 to 4~~claim 1, wherein the first pin junction part further comprises a second i-layer disposed between the first p-layer and first n-layer and constituted by a mainly amorphous silicon film.

6. (Currently Amended) A photoelectric transducer according to ~~one of claims 1 to~~ 4claim 1, further comprising a second pin junction part, disposed in series with the first pin junction part, including:

a second p-layer;

a second n-layer disposed so as to oppose the second p-layer; and

a third i-layer disposed between the second p-layer and second n-layer and made of an amorphous silicon film.

7. (Original) A photoelectric transducer apparatus comprising:

a substrate;

a first electrode layer disposed on one side of the substrate;

a second electrode layer disposed so as to oppose the first electrode layer; and

a first pin junction part including a first n-layer formed on the first electrode layer, a first p-layer formed on one side of the second electrode layer so as to oppose the first n-layer, and a first i-layer, disposed between the first p-layer and first n-layer, containing an iron atom, a silicon atom bonded to the iron atom, and a hydrogen atom.

8. (Original) An iron silicide film for constructing an i-layer in a pin junction;

the iron silicide film containing an iron atom, a silicon atom bonded to the iron atom, and a hydrogen atom while being mainly amorphous.

9. (New) A photoelectric transducer according to claim 2, wherein the first i-layer is mainly amorphous.

10. (New) A photoelectric transducer according to claim 2, wherein the first i-layer has a hydrogen atom content of 1 to 25 atom %.

11. (New) A photoelectric transducer according to claim 3, wherein the first i-layer has a hydrogen atom content of 1 to 25 atom %.

12. (New) A photoelectric transducer according to claim 2, wherein the first pin junction part further comprises a second i-layer disposed between the first p-layer and first n-layer and constituted by a mainly amorphous silicon film.

13. (New) A photoelectric transducer according to claim 3, wherein the first pin junction part further comprises a second i-layer disposed between the first p-layer and first n-layer and constituted by a mainly amorphous silicon film.

14. (New) A photoelectric transducer according to claim 4, wherein the first pin junction part further comprises a second i-layer disposed between the first p-layer and first n-layer and constituted by a mainly amorphous silicon film.

15. (New) A photoelectric transducer according to claim 2, further comprising a second pin junction part, disposed in series with the first pin junction part, including:

a second p-layer;

a second n-layer disposed so as to oppose the second p-layer; and

a third i-layer disposed between the second p-layer and second n-layer and made of an amorphous silicon film.

16. (New) A photoelectric transducer according to claim 3, further comprising a second pin junction part, disposed in series with the first pin junction part, including:

a second p-layer;

a second n-layer disposed so as to oppose the second p-layer; and

a third i-layer disposed between the second p-layer and second n-layer and made of an amorphous silicon film.

17. (New) A photoelectric transducer according to claim 4, further comprising a second pin junction part, disposed in series with the first pin junction part, including:

a second p-layer;

a second n-layer disposed so as to oppose the second p-layer; and

a third i-layer disposed between the second p-layer and second n-layer and made of an amorphous silicon film.